Two-dimensional materials and applications

6. Analytical Tools for 2D Materials







Scanning Tunneling Microscopy VB SL MoS. f CB nm Grain II Grain I Grain II +3.5 +2.5 +1.5 Grain I d//d // (a.u.) +0.6 Bare +0.3 graphite -1.55 V-٥ 🛦 Grain boundary е A -1.0 Conduction band -1.0 A -2.0 -0.5 (ve) version (version (version version (version version versio 4 -3.0 Grain 2 Grain 4 -4.0 Grain 2.0 S. 05 05,0 00 2.5 10 20 3.0 Bias (V) \$\$\$\$\$\$\$\$0123 Distance (nm) Yu Li Huang et al. Nat.Comm 6, 7298 (2015)

Conductive-AFM



F. Giannazzo et al. PRB 92, 081307 (2015)

Kelvin Probe Force Microscopy



M. Tosun et al. Sci.Rep 5, 10990 (2015)

Piezo Force Microscopy



subatomic deformation-induced vertical piezoelectricity of CdS





Zhu, H. et al. Nat. Nanotechnol. 10, 151 (2015) Wang, X. et al. Sci. Adv. 2, e1600209 (2016)



Wu et al. AIP Advances 8, 055016 (2018)



G. Lee et al. Science 340, 1073 (2013)



Friction Force Microscopy





C. Lee et al. Sci. 328, 76 (2010)

Peak Force Tapping Microscopy





Raman spectrum of graphene



Raman is powerful tool to analyze quality of graphene. To avoid damaging the graphene, laser spot power of less than 1 mW must be used for a laser spot diameter of 500 nm or greater and acquisition times of less than 30 seconds and it is recommended to include a range from 1150 cm⁻¹ to 3100 cm⁻¹

Disorder of graphene

- The values of I_D/I_G should be recorded as the measurands for the level of disorder of the graphene. For low and moderate defect density, I_D/I_G increases with an increasing defects density.

Evidence of monolayer graphene

- 1. 2D-peak must be a single Lorentzian peak
- 2. FWHM of 2D of \leq 35 cm⁻¹, where I_D/I_G \leq 0.2.
- 3. $I_{2D}/I_G > 2$ (However, this ratio can be reduced by other factors such as the level of disorder and doping and as such it cannot be explicitly used as an indication of single layer graphene.)

Mismatch of bilayer graphene

Mismatch angle is low (<5°) : the presence of additional peaks at either 1370~470 cm⁻¹ or 1540~1620 cm⁻¹ must first be assessed. If these peaks are not observed, the sheet could be single layer or twisted-bilayer with a higher (>5°) mismatch angle between the two layers

Graphene



Graphene defect



A. Eckmann et al. Nano Lett. (2012) & L.G Cancado et al. Nano Lett. (2011) & L. G. Cancado et al. 2D Mater. (2017) & G.H. Lee Nature Comm (2014)

Stacking sequence





L. Liang et al. Nanoscale (2017) & X. Zhang et al. Carbon (2016)

Doping and strain of graphene





Out-of-plane A_{1q} mode

- The interaction between sulfur atoms of neighboring layers can influence the frequency.
- single layer → double layer, adds an additional spring (binding force) leads to an increase of the A_{1a}-mode frequency with increasing number of layers.
- Binding force leads to an increase of frequency the weak interlayer interaction.

In-plane E¹_{2q} mode

- The self-interaction terms for Mo and S influence to decrease the frequency with increasing number of layers. (opposite to the result of A_{1α} mode)
- Change in frequency is associated to the differences in the lattice constant and interatomic distances in bulk and the single layer, respectively.
- The decrease of the E¹_{2g} phonon frequency is associated with a stronger dielectric screening of the long-range Coulomb interaction in few-layer and bulk MoS₂.



A. C. Ferrari et al. Nature nanotechnol. (2013) & F. Bonaccorso et al. ACS Nano (2013) & C. Lee et al. ACS Nano (2010)

Layer dependence

 WS_2



P. Tonndorf et al. Optics Express (2013) & Yamamoto et al, ACS Nano (2014) & Zeng et al. Sci. Rep. (2013) & W. Zhao et al. Nanoscale (2013)

슬라이드 12

S4 peak간 간격, B12g peak으로 layer 판별 Sojung_NCML, 2020-05-18

S5 polarized Raman Sojung_NCML, 2020-05-18

S6 A1g가 점점 커지면서 동시에 1-2L에서는 single line 3-4L에서는 2개, 5L에서는 3개로 split됨 (Davydov split) B12g는 1L에 없고, 2L에서 가장 prominent함 Sojung_NCML, 2020-05-18 Sojung_NCML, 2020-05-18

Defect induced Raman



Doping and strain



S. Mignuzzi et al. PRB (2015) & R. Rao et al PRB (2019)

Polarized Raman



Xia et al. Nat. Comm. (2014)

Analytical Tools for 2D Materials: Photoluminescence



Mak et al. PRL (2010) & Radisavljevic et al. Nat. Nano (2011) & Splendiani et al. Nano Lett (2010) & Kappera et al Nat. Mater. (2014) & Tran et al. PRB (2014) & Yang et al. Light Sci. Appl. (2015) & Castellanos-Gomez et al. J. Phys. Chem. Lett. (2015) & Mak et al. Nat. Mater. (2012) & Ross et al. Nat. Commun. (2013)

Analytical Tools for 2D Materials: Photoluminescence

Low temperature PL of MoS₂ (50 K)



Non-radiative pathway is suppressed because phonon states are less populated at low temperature around bound exciton.







Smaller dark exciton energy than bright exciton for WSe₂

* Dark exciton involves e- and h+ in different valleys resulting in momentum-forbidden states, which cannot emit photons



Verhagen et al. Nanoscale (2020) & Edelberg et al. Nano Lett. (2019) & Amani et al. Science (2015)

Analytical Tools for 2D Materials: Raman & PL mapping

OM

9 µm

6.000 5,000 4,000 1.500 3.000 1000 2,000 500 1,000 $I_{-}(xy)$ $I_{G}(x,y)$ $I_{2D}(x,y)$ 3000 8 000 7.000 2.500 800 6,000 2,000 5 0 0 0 1.500 4,000 3,000 1.000 2,000

Raman mapping of CVD-grown graphene

Wrinkled MoS₂

а 4000 S Mo Pre-strained elastomeric 3500 а WL Source substrate 3000 2500 2000 Deposition of MoS₂ by mechanical exfoliation 1500 1000 compressive 500 The strain is relased 375 385 9 405 Raman shift (cm⁻¹) 410 380 415 Wrinkled MoS₂ -Flat MoS₂ Wrinkled MoS₂ 3 μή) 1000 sity MoSe 500 -600 550 650 700 750 Wavelength (nm)

Q. Yu et al. Nat. Mater. (2011) & Zafar et al. Adv. Funct. Mater. (2019) & Castellanos-Gomez et al. Nano Lett. (2013) & Alexeev et al. Nano Lett. (2017)

PL mapping of CVD-grown WS₂

10 um (vii) (ix) (viii) 350 400 450 Wavenumber (cm⁻¹)

PL imaging using bright-field optical microscope

(iv) (vi) (v)2.1 1.8 1.9 2.0 ΡL Photon Energy (eV) Bright Regio Raman



S2 S3

- S2 sulfur vacancy rich region이 더 밝은 것이 맞습니다. 우리가 평소 생각하는 Vs에 따라 PL이 떨어지는 것은 perfect crystal 대비했을 경우이고, W vacancy가 많으면 deep level 형성되어 pl이 줄어듭니다. Sojung_NCML, 2020-05-18
- S3 https://onlinelibrary.wiley.com/doi/full/10.1002/adma.201605043 Sojung_NCML, 2020-05-18

Hydrogenated graphene

Binding energy (eV)



Gowda et al. ACS AMI (2014) & Johra et al. J. Ind. Eng. Chem. (2014) & Ko et al. ACS AMI (2018)

Second harmonic generation (SHG)



Y. Li et al Nano Lett. (2013) & W.-T. Hsu et al ACS Nano (2014)



P. Huang et al. Nature (2011) & G. H. Lee et al. Science (2013)

TEM image of graphene

Monolayer graphene



Bilayer graphene



Monolayer graphene the outer hexagon intensity is similar with inner one. On the other hand, bilayer graphene the outer hexagon intensity is greater than the inner one.



Thickness of graphene flakes

Misoriented angle (θ) of graphene layers



Misoriented bilayer graphene regions are easily identified by the presence of 12 spots in each ring rather than the 6 observed for single layer graphene or AB stacked graphite. The misoriented bilayer graphene also reveals a Moiré pattern.

Crystal Structure of Graphene



P. Huang et al. Nature (2011) & G. H. Lee et al. Science (2013)

Boron Nitride



MoS₂





A. van der Zande et al. Nature Mater. (2013)





Diffraction pattern

Fluorinated graphene





 $a_{1}, a_{2} = 0.246 \text{ nm}$



MoTe₂ phase transition







Kashtiban et al. Nat. Commun. (2014) & G.H. Lee et al. in preparation

Defect observation of WS₂





MoS₂



Reknitting graphene





Moiré pattern

Twisted angle of CVD graphene



Strain engineered TMD superlattice



P.-Y. Chen et al. Adv. Mater (2019) & Brown et al. Nano Lett. (2012) & S. Xie et al. Science (2018)